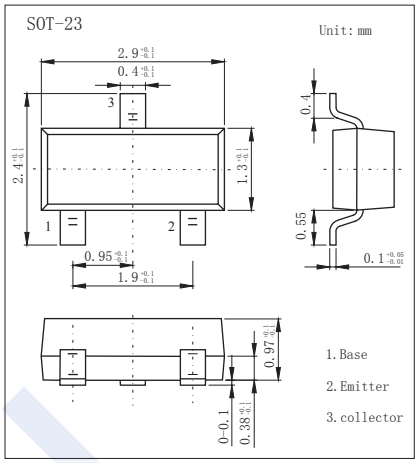
PNP Transistors

2SA1365



■ Features

- Low collector to emitter saturation voltage.
- Excellent linearity nof DC forward current gain.
- Super mini package for easy mounting.
- High collector current.
- High gain band width product.
- Complementary to 2SC3440

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	-25	V
Collector - Emitter Voltage	V_{CEO}	-20	
Emitter - Base Voltage	V_{EBO}	-4	
Collector Current - Continuous	I_C	-700	mA
Peak Collector Current	I_{CM}	-1	A
Collector Power Dissipation	P_C	150	mW
Junction Temperature	T_J	150	℃
Storage Temperature range	T_{stg}	-55 to 150	

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	I_C= -100 μA, I_E=0	-25			V
Collector- emitter breakdown voltage	V_{CEO}	I_C= -1 mA, I_B=0	-20			
Emitter - base breakdown voltage	V_{EBO}	I_E= -100 μ A, I_C=0	-4			
Collector-base cut-off current	I_{CBO}	V_{CB}= -25 V , I_E=0			-100	nA
Emitter cut-off current	I_{EBO}	V_{EB}= -2V , I_C=0			-100	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-500mA, I_B=- 25mA		-0.2	-0.5	V
Base - emitter saturation voltage	$V_{BE(sat)}$	I_C=-500mA, I_B=- 25mA			-1.2	
DC current gain *	h_{FE}	V_{CE}= -4V, I_C= -100mA	150		800	
Transition frequency	f_T	V_{CE}= -6V, I_E= 10mA	100	180		MHz

* It shows h_{FE} classification in right table.

■ Classification of h_{fe}

Marking	AE	AF	AG
hFE	150～300	250～500	400～800

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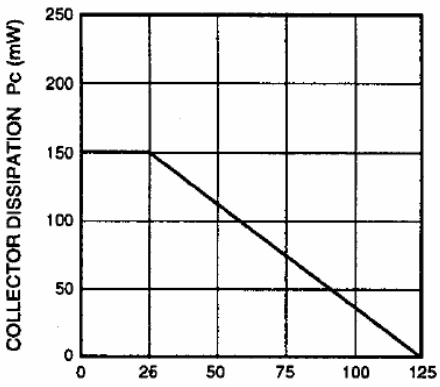
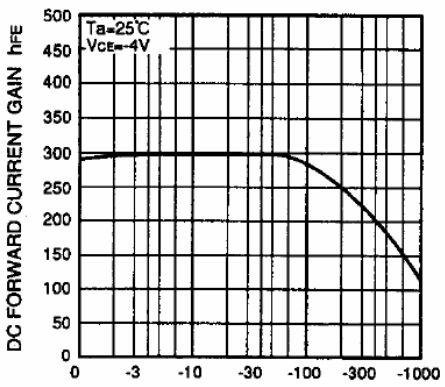
■ Typical Characterisitics

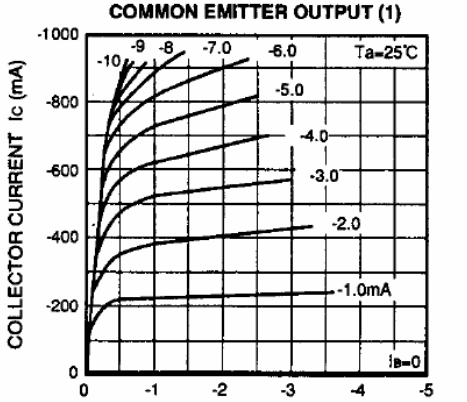
COLLECTOR DISSIPATION VS. AMBIENT TEMPERATURE



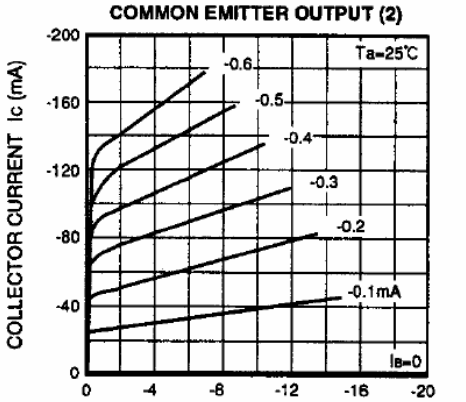
DC FORWARD CURRENT GAIN VS. COLLECTOR CURRENT



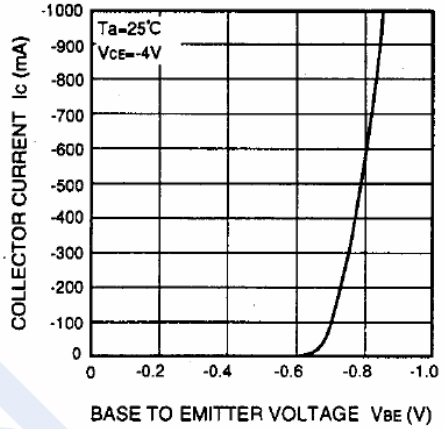
COMMON EMITTER OUTPUT (1)



COMMON EMITTER OUTPUT (2)



COMMON EMITTER TRANSFER (1)



COMMON EMITTER TRANSFER(2)